Electronic Supplementary Information

for

Unexpected efficiency enhancement of flexible dye-sensitized solar cells by repeated outward bending

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Figure S1 Typical XRD pattern for the commercial P25 TiO₂.
Figure S3 illustrates a generalized equivalent circuit for a complete DSC, where $R_s$ is the equivalent series resistance, $R_{CO}$ and $C_{CO}$ stand for the resistance and capacitance at the TCO/TiO$_2$ interface, respectively. $R_{TCO}$ and $C_{TCO}$ represent the resistance and capacitance at the exposed TCO/electrolyte interface, respectively. $R_t$ represents the electron transport resistance in the TiO$_2$ film, while $R_{ct}$ stands for the charge transfer resistance at the TiO$_2$/dye/electrolyte interface. $C_{\mu}$ represents the capacitance of TiO$_2$ film, and $Z_D$ stands for the Nernst diffusion resistance of the electrolyte. $R_{Pt}$ and $C_{Pt}$ stand for the charge

Figure S2 Photovoltaic performance before bending and after 10000 cycles of bending with a radius of 18 mm.
transfer resistance and electric double layer capacitance at the Pt/electrolyte interface, respectively.

Figure S3  Equivalent circuit for the flexible DSC.